

1. General description

Dual Silicon Carbide Schottky diodes in a TO3PF plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- Insulated package rated at 2500V RMS

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

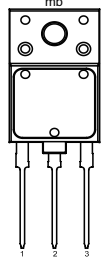
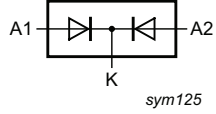
4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Notes | Values | | | Unit |
|--------------------------------|---------------------------------|--|-------|------------|------|------|------|
| Absolute maximum rating | | | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | | 650 | | | V |
| $I_{O(AV)}$ | average forward current | $\delta = 0.5$; square-wave pulse; $T_h \leq 15$ °C; both diodes conducting; Fig. 1 ; Fig. 2 ; Fig. 3 | | 20 | | | A |
| T_j | junction temperature | | | -55 to 175 | | | °C |
| Symbol | Parameter | Conditions | Notes | Min | Typ | Max | Unit |
| Static characteristics | | | | | | | |
| V_F | forward voltage | $I_F = 10$ A; $T_j = 25$ °C; per diode; Fig. 5 | | - | 1.45 | 1.70 | V |
| | | $I_F = 10$ A; $T_j = 150$ °C; per diode; Fig. 5 | | - | 1.80 | 2.20 | V |
| Dynamic characteristics | | | | | | | |
| Q_r | recovered charge | $I_F = 10$ A; $di_F/dt = 500$ A/ μ s; $V_R = 400$ V; $T_j = 25$ °C; per diode; Fig. 7 | | - | 14.5 | - | nC |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|---|---|
| 1 | A1 | anode |  |  sym125 |
| 2 | K | cathode | | |
| 3 | A2 | anode | | |
| mb | n.c. | mounting base; isolated | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|---------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| WNSC5D20650CJ | TO3PF | WNSC5D20650CJ6Q | Tube | 30 | SOT1293 | 16-Mar-2006 |

7. Marking

Table 4. Marking codes

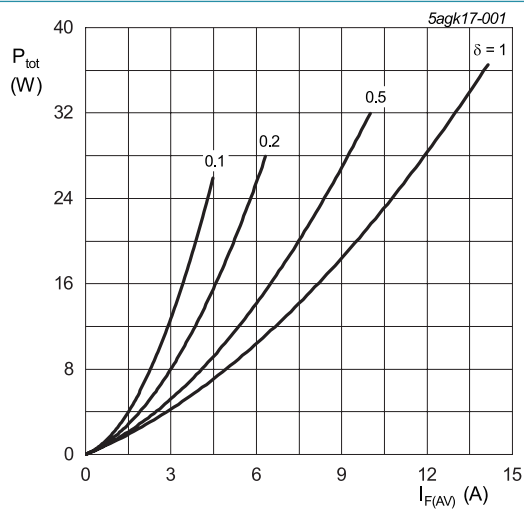
| Type number | Marking codes |
|---------------|-------------------|
| WNSC5D20650CJ | WNSC5D 20650CJ |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Notes | Values | Unit |
|------------------|-------------------------------------|--|-------|------------|----------------------|
| V_{RRM} | repetitive peak reverse voltage | | | 650 | V |
| V_{RWM} | crest working reverse voltage | | | 650 | V |
| V_R | reverse voltage | DC | | 650 | V |
| $I_{O(AV)}$ | average forward current | $\delta = 0.5$; square-wave pulse; $T_h \leq 15^\circ\text{C}$; both diodes conducting; Fig. 1; Fig. 2; Fig. 3 | | 20 | A |
| I_{FRM} | repetitive peak forward current | $\delta = 0.5$; $t_p = 25\ \mu\text{s}$; $T_h \leq 60^\circ\text{C}$; square-wave pulse; per diode | | 20 | A |
| I_{FSM} | non-repetitive peak forward current | $t_p = 10\ \text{ms}$; $T_{j(\text{init})} = 25^\circ\text{C}$; sine-wave pulse; per diode | | 45 | A |
| | | $t_p = 10\ \mu\text{s}$; $T_{j(\text{init})} = 25^\circ\text{C}$; square-wave pulse; per diode | | 540 | A |
| I^2t | I^2t for fusing | sine-wave pulse; $T_{j(\text{init})} = 25^\circ\text{C}$; $t_p = 10\ \text{ms}$ | | 10.125 | A^2s |
| T_{stg} | storage temperature | | | -55 to 175 | $^\circ\text{C}$ |
| T_j | junction temperature | | | -55 to 175 | $^\circ\text{C}$ |



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 1.103\ \text{V}; R_s = 0.1048\ \Omega$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

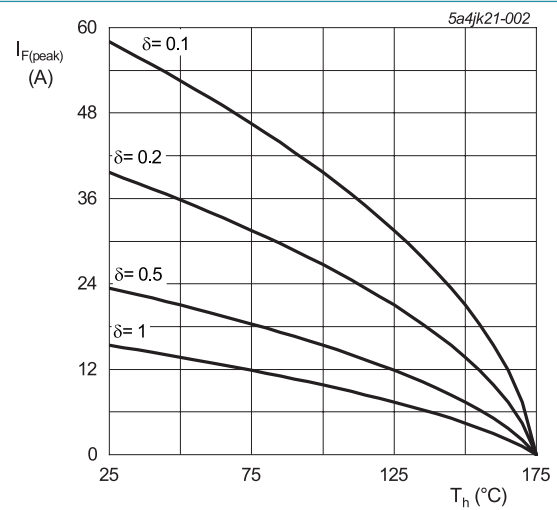


Fig. 2. Current derating as a function of heatsink temperature; per diode

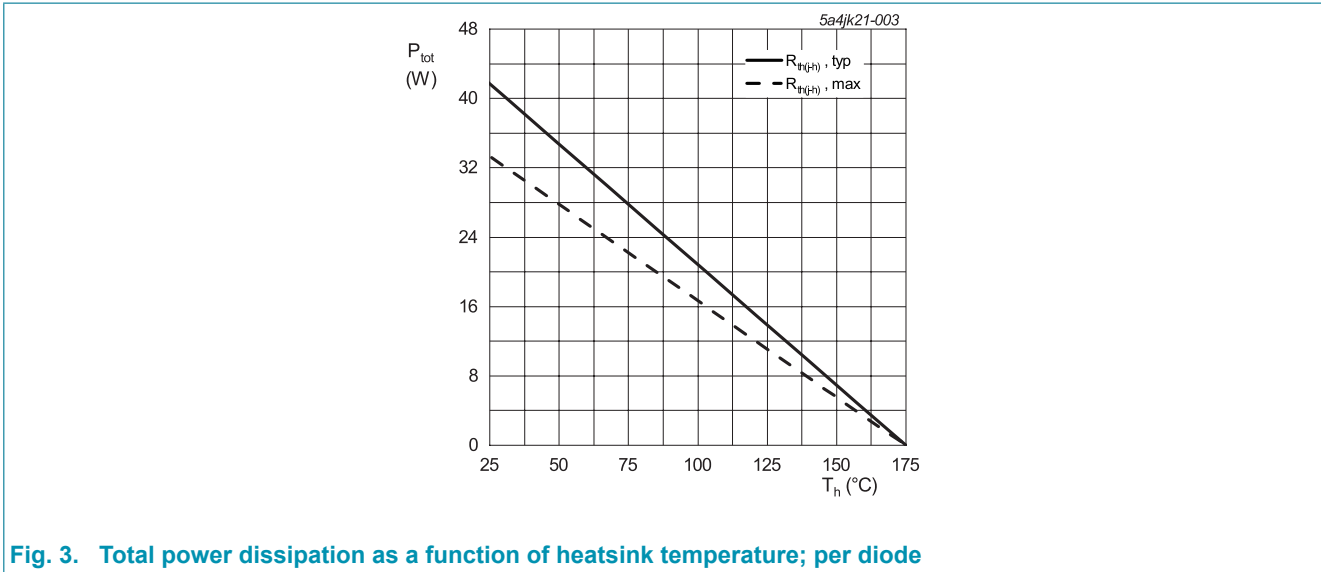


Fig. 3. Total power dissipation as a function of heatsink temperature; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------|--|--|-----|-----|-----|------|
| $R_{th(j-h)}$ | thermal resistance from junction to heatsink | with heatsink compound; per diode; Fig. 4 | - | 3.6 | 4.5 | K/W |
| | | with heatsink compound; both diodes conducting | - | 2.5 | 3.4 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | in free air | - | 60 | - | K/W |

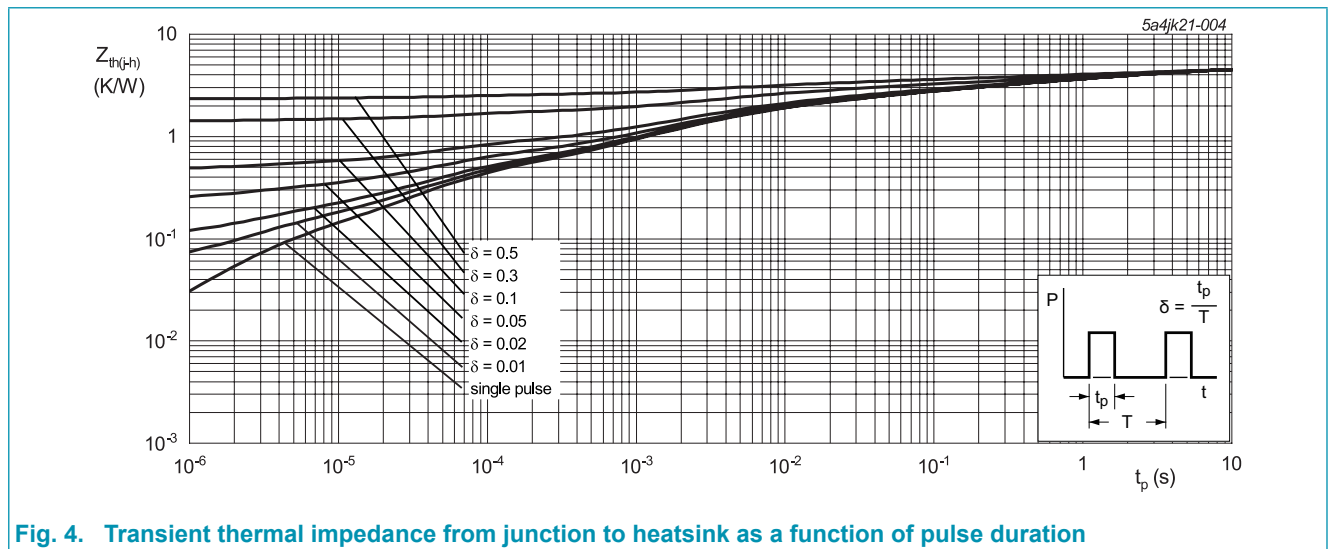


Fig. 4. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

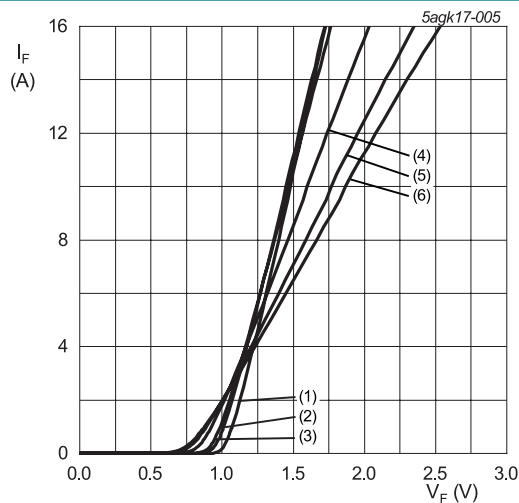
Table 7. Isolation characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------------|-----------------------|--|-----|-----|------|------|
| $V_{isol(RMS)}$ | RMS isolation voltage | $50 \text{ Hz} \leq f \leq 60 \text{ Hz}$; $RH \leq 65 \%$; from all pins to external heatsink; sinusoidal waveform; clean and dust free | - | - | 2500 | V |
| C_{isol} | isolation capacitance | $f = 1 \text{ MHz}$; from cathode to external heatsink | - | 10 | - | pF |

11. Characteristics

Table 8. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------|--|-----|------|------|---------------|
| Static characteristics | | | | | | |
| I_F | forward current | $I_F = 10 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 5 | - | 1.45 | 1.70 | V |
| | | $I_F = 10 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$ per diode; Fig. 5 | - | 1.80 | 2.20 | V |
| | | $I_F = 10 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ per diode; Fig. 5 | - | 2.00 | 2.30 | V |
| I_R | reverse current | $V_R = 650 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 6 | - | 0.5 | 50 | μA |
| | | $V_R = 650 \text{ V}; T_j = 175 \text{ }^\circ\text{C};$ per diode; Fig. 6 | - | 25 | 250 | μA |
| Dynamic characteristics | | | | | | |
| Q_r | recovered charge | $I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 7 | - | 14.5 | - | nC |
| C_d | diode capacitance | $f = 1 \text{ MHz}; V_R = 1 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 320 | - | pF |
| | | $f = 1 \text{ MHz}; V_R = 300 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 38 | - | pF |
| | | $f = 1 \text{ MHz}; V_R = 600 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 36 | - | pF |
| E_{as} | non-repetitive avalanche energy | $I_R = 4.9 \text{ A}; L = 5 \text{ mH}; T_{j(\text{init})} = 25 \text{ }^\circ\text{C};$ per diode | 60 | - | - | mJ |



$V_o = 1.103 \text{ V}; R_s = 0.1048 \text{ } \Omega$
 (1) $T_j = -55 \text{ }^\circ\text{C};$ typical values
 (2) $T_j = 0 \text{ }^\circ\text{C};$ typical values
 (3) $T_j = 25 \text{ }^\circ\text{C};$ typical values
 (4) $T_j = 100 \text{ }^\circ\text{C};$ typical values
 (5) $T_j = 150 \text{ }^\circ\text{C};$ typical values
 (6) $T_j = 175 \text{ }^\circ\text{C};$ typical values

Fig. 5. Forward current as a function of forward voltage; typical values; per diode

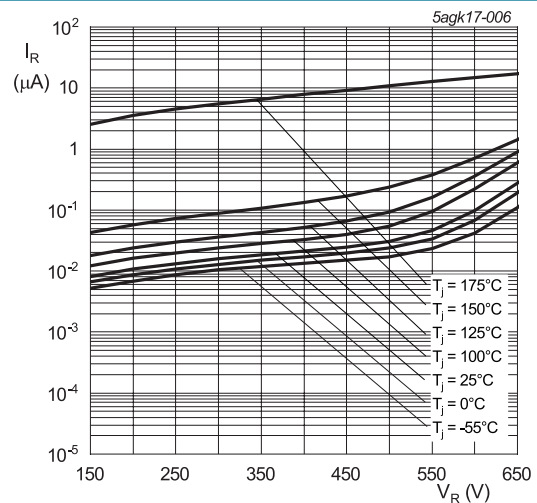


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode

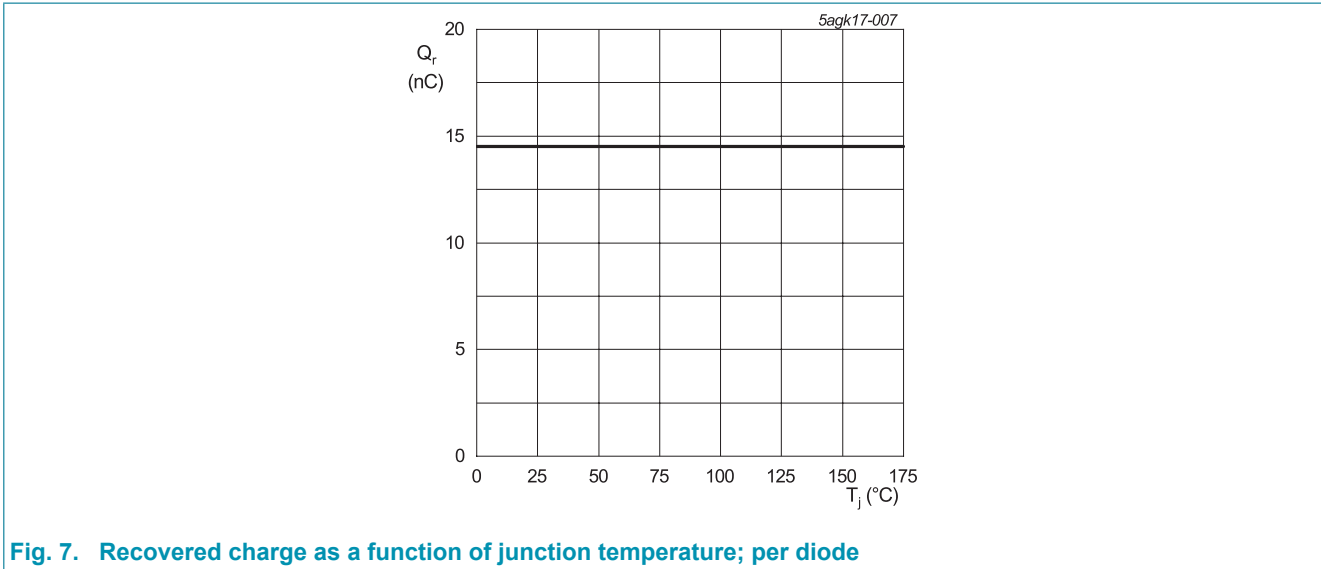
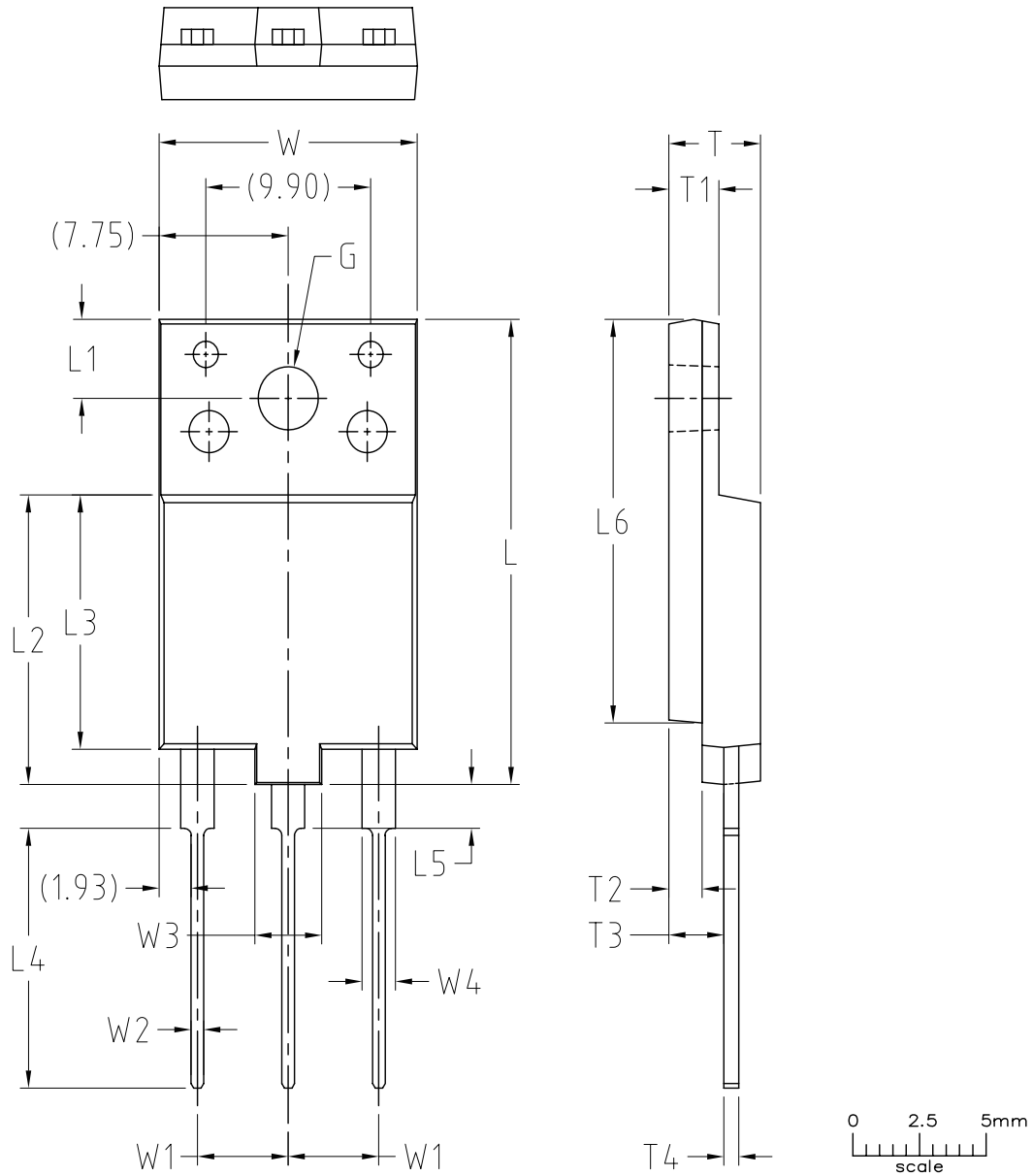


Fig. 7. Recovered charge as a function of junction temperature; per diode

12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-3P 'full pack' TO3PF



Remark : (X) the dimension X in brackets is for reference

| UNIT | W | W1 | W2 | W3 | W4 | L | L1 | L2 | L3 | L4 | L5 | L6 | T | T1 | T2 | T3 | T4 | G(φ) |
|------|------|------|------|------|------|------|-----|------|------|------|-----|------|-----|-----|-----|-----|-----|------|
| mm | 15.7 | 5.75 | 0.95 | 4.20 | 2.20 | 26.7 | 4.6 | 16.7 | 14.7 | 15.0 | 2.7 | 23.2 | 5.7 | 3.2 | 2.2 | 3.5 | 1.1 | 3.8 |
| | 15.3 | 5.15 | 0.65 | 3.80 | 1.80 | 26.3 | 4.4 | 16.3 | 14.3 | 14.6 | 2.3 | 22.8 | 5.3 | 2.8 | 1.8 | 3.1 | 0.8 | 3.4 |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|--------|------|--|---------------------|------------|
| | IEC | JEDEC | EIAJ | | | |
| | | TO-3PF | | | | |

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
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- [2] The term 'short data sheet' is explained in section "Definitions".
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